

Low-frequency noise in GaAs and InP Schottky diodes

K.F. Sato, C.W. Chan, K. Najita, M.P. DeLisio, Y.H. Chung, J. Cowles, P.C. Grossman, R. Lai, A.K. Oki, D.C. Streit and H. Wang. "Low-frequency noise in GaAs and InP Schottky diodes." 1998 MTT-S International Microwave Symposium Digest 98.3 (1998 Vol. III [MWSYM]): 1695-1698.

This paper examines the low-frequency noise properties of millimeter-wave GaAs and InP Schottky diodes. Measurements of diodes fabricated using both HEMT and HBT epitaxy will be presented. These noise measurements should enable the development of accurate models useful in the analysis and design of MMIC components.

 [Return to main document.](#)